multicomp PRO





Pin Configuration:

- 1. Collector
- 2. Base
- 3. Emitter

Features:

- PNP Silicon Planar Switching Transistor
- General Purpose Switching and Amplifier Applications

Absolute Maximum Ratings

Description	Symbol	Value	Unit	
Collector-Emitter Voltage	V _{CEO}	40		
Collector-Base Voltage	V _{CBO}	40	V	
Emitter-Base Voltage	V _{EBO}	5		
Collector Current Continuous	Ι _C	200	mA	
Power Dissipation at T _a = 25°C Derate above 25°C	D	625 5	mW mW/°C	
Power Dissipation at T _c = 25°C Derate above 25°C		1.5 12	W mW/°C	
Operating and Storage Junction Temperature Range	T _j , T _{stg}	-55 to +150	°C	
Thermal Resistance	*	~	~	

Junction to Case	R _{th (j-c)}	125	°C/W
Junction to Ambient	R _{th (j-a)}	200	C/W

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Electrical Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Description	Symbol	Test Condition	2N3906	Unit	
Collector-Emitter Voltage	V _{CEO} *	$I_{\rm C} = 1$ mA, $I_{\rm B} = 0$			
Collector-Base Voltage	V _{CBO}	Ι _C = 10μΑ, Ι _E = 0	>40	V	
Emitter-Base Voltage	V _{EBO}	Ι _Ε = 10μΑ, Ι _C = 0	>5		
Collector-Cut off Current	I _{CEX}		.50		
Emitter-Cut off Current	I _{BL}	V _{CE} = 30V, V _{EB} = 3V	<50	nA	
DC Current Gain	h _{FE} *	$I_{C} = 0.1\text{mA}, V_{CE} = 1V$ $I_{C} = 1\text{mA}, V_{CE} = 1V$ $I_{C} = 10\text{mA}, V_{CE} = 1V$ $I_{C} = 50\text{mA}, V_{CE} = 1V$ $I_{C} = 100\text{mA}, V_{CE} = 1V$	>60 >80 100 - 300 >60 >30	-	
Collector Emitter Saturation Voltage	V _{CE (sat)} *	I _C = 10mA, I _B = 1mA	<0.25 <0.4		
Base Emitter Saturation Voltage	V _{BE (sat)} *	I _C = 50mA, I _B = 5mA	0.65 - 0.85 <0.95	V	
Small Signal Characteristic			· · · · · ·		
Transistors Frequency	f _T	I _C = 10mA, V _{CE} = 20V, f = 100MHz	>250	MHz	
Output Capacitance	C _{ob}	V _{CB} = 5V, I _E = 0, f = 100kHz	<4.5		
Input Capacitance	C _{ib}	V _{BE} = 0.5V, I _C = 0, f = 100kHz	<10 pF		
			400 400		

	ID ID	DL C		
Small Signal Current Gain	h _{fe}		100 - 400	-
Input Impedance	h _{ie}	All f = 1kHz	2 - 12	kΩ
Output Admittance	h _{oe}	I _C = 1mA, V _{CE} = 10V	3 - 6	μΩ
Voltage Feedback Ratio	h _{re}		1 - 10	× 10 ⁻⁴
Noise Figure	NF	I _C = 100μA, V _{CE} = 5V R _s = 1kΩ f = 10Hz to 15.7kHz	<40	dB

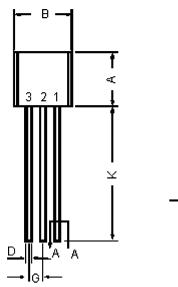
Switching Time

Delay Time	t _d	V _{CC} = 3V, V _{BE} = 0.5V	<35	
Rise Time	t _r	I _C = 10mA, I _{B1} = 1mA	~30	22
Storage Time	t _s	V _{CC} = 3V, I _C = 10mA	<225	ns
Fall Time	t _f	I _{B1} = I _{B2} = 1mA	<75	

*Pulse Condition : Pulse Width = 300µs, Duty Cycle = 2%.

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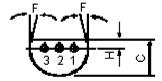






Dimensions	Min.	Max.	
Dimensions		INICA.	
А	4.32	5.33	
В	4.45	5.2	
С	3.18	4.19	
D	0.41	0.55	
E	0.35	0.5	
F	5°		
G	4.4.4	1.4	
Н	1.14	1.53	
К	12.7	-	

Dimensions : Millimetres



Pin Configuration:

- 1. Collector
- 2. Base
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Part Number Table

Description	Part Number	
Transistor, PNP, TO-92	2N3906	

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